In The Specification:

Please amend paragraph [0010] as follows:

--In accordance with the object described above, the present invention discloses a double-triggered silicon controlling rectifier, comprising a P-type substrate, a plurality of N+ diffusion areas, a plurality of P+ diffusion areas, a plurality of isolation structures, a first, a second and a third N-well regions. The first, the second and the third N-well regions are all formed within the P-type substrate. The second and the third N-well regions are formed on each side of the first N-well region, opposite to the each other. The plurality of N+ diffusion areas comprises: a first N+ diffusion area, formed in the first N-well region and coupled to an external power terminal; a second N+ diffusion area, formed in the first N-well region and on one side of the first N+ diffusion area, as a N-type trigger terminal of the double-triggered silicon controlling rectifier; a third N+ diffusion area, formed in the first N-well region and on another side of the first N+ diffusion area, opposite to the second N+ diffusion area as the N-type trigger terminal of the double-triggered silicon controlling rectifier; a fourth N+ diffusion area, partially formed in the third N-well region and partially formed in the P-type substrate, and on one side of the second N+ diffusion region, opposite to the first N+ diffusion region as a cathode of the double-triggered silicon controlling rectifier; and a fifth N+ diffusion, partially formed in the ~~third~~ second N-well region and partially formed in the P-type substrate, and on one side of the third N+ diffusion region, opposite to the first N+ diffusion region as the cathode of the double-triggered silicon controlling rectifier. The plurality of P+ diffusion areas comprises: a first P+ diffusion area, formed within the first N-well region

and between the first N+ diffusion area and the second N+ diffusion area, as an anode of the double-triggered silicon controlling rectifier; a second P+ diffusion area, formed within the first N-well region and between the first N+ diffusion area and the third N+ diffusion area, as the anode of the double-triggered silicon controlling rectifier; a third P+ diffusion area, formed within the P-type substrate between the first and the third N-well regions, and between the second and the fourth N+ diffusion areas, as a P-type trigger terminal of the double-triggered silicon controlling rectifier; a fourth P+ diffusion area, formed within the P-type substrate between the first and the second N-well regions, and between the third and the fifth N+ diffusion areas, as the P-type trigger terminal of the double-triggered silicon controlling rectifier; a fifth P+ diffusion area, formed within the P-type substrate and on one side of the fourth N+ diffusion area, opposite to the third P+ diffusion area, as a ground terminal of the double-triggered silicon controlling rectifier; and a sixth P+ diffusion area, formed within the P-type substrate and on one side of the fifth N+ diffusion area, opposite to the fourth P+ diffusion area, as the ground terminal of the double-triggered silicon controlling rectifier. The plurality of isolation structures are formed within the P-type substrate and between spaces of the pluralities of N+ and P+ diffusion areas.--